

EFFECT OF SUBSTRATE TEMPERATURE AND ANNEALING ON THE ELECTRICAL PROPERTIES OF LEAD PHTHALOCYANINE THIN FILMS

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ABSTRACT

Lead phthalocyanine (PbPc) thin films are prepared at different substrate temperatures on microglass slides of size 75 x 25 x 1.3 mm by thermal evaporation technique, at a base pressure of 10⁻⁵ m.bar. Films of equal thickness coated at room temperature are annealed in air and in vacuum at different temperatures for one hour. The electrical conductivity observations are made in the temperature range 300 to 580 K. The thermal activation energies are calculated from the Arrhenius plots. It is observed that the thermal activation energy in the intrinsic region decreases with increase in substrate temperature and increases with increase in annealing temperature.

Key words: Lead phthalocyanine, Thin films, Thermal evaporation.

INTRODUCTION

Phthalocyanines form a class of organic semiconductors. These are materials with a wide range of applications due to their stability against thermal and chemical decomposition and intense optical absorption in the visible region of the spectrum. They are used in gas sensors¹, in electro topography and solar cells^{2,3}, as dyes in textile and paint industries⁴, and in opto–electronic devices⁵. They are also used in electro–chromic display devices, photodynamic reagents and electro–catalysts for fuel cells^{6,7}. Measurements have shown that freshly evaporated PbPc films absorb oxygen at room temperature over a period of several days⁸ and distinct differences are observed in fresh, air exposed and subsequently annealed PbPc films⁹. The electrical behaviour of PbPc thin films in the triclinic phase, when exposed to both oxygen and dry air for various periods, are reported¹⁰. PbPc thin films can be effectively used to sense toxic NO₂ gas¹¹.

Conduction in PbPc thin films with aluminium electrodes are already reported¹². It has become apparent that the progress in the development of active materials for molecular

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electronics, based on PbPc thin films require a more comprehensive knowledge of its material properties. In this paper, the electrical properties of PbPc thin films of thickness 2400 Å coated at different substrate temperatures and films subjected to post–deposition annealing in air and vacuum are studied. The thermal activation energies are calculated in each case.

EXPERIMENTAL

PbPc in the powder form (99.99% pure) obtained from Aldrich is used as the source material. The samples are prepared in a "Hindi Hi Vac" vacuum coating unit (Model No. 12A4). Thermal evaporation technique is used for film preparation 13. The films are coated on thoroughly cleaned glass substrates kept at different temperatures, at a base pressure of 10⁻⁵ m.bar. The thickness of the films are controlled by a single crystal thickness monitor and are cross—checked by Tolansky's multiple beam interferometry method 14. Samples are annealed in air for one hour in a specially designed furnace provided with a digital temperature controller cum recorder. Films of the same thickness are annealed in vacuum also. The electrical conductivity measurements of these samples are conducted by keeping them in a conductivity cell at a pressure of 10⁻³ m.bar. The resistances of the films are measured using a Keithley programmable electrometer, Model No. 617 between an approximate temperature range of 300 to 580 K. Ohmic contacts are made with silver electrodes and silver paste.

RESULTS AND DISCUSSION

The electrical conductivity is given by $\sigma = L/Rbt$ where L is the length, R is the resistance, b is the breadth and t is the thickness of the film. The temperature dependence of conductivity is given by Arrhenius equation $\sigma = \sigma_0 \exp{(-E_T/kT)}$ where σ_0 is the pre–exponential factor, E_T is the thermal activation energy, k is Boltzmann constant and T is the absolute temperature.

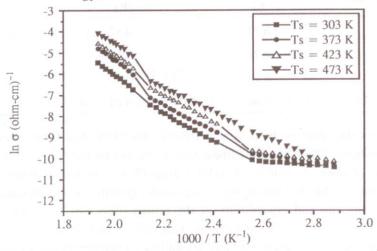


Fig. 1. Plots of ln σ versus 1000/T for PbPc thin films coated at different substrate temperatures

Plots of $\ln \sigma$ versus 1000/T show three linear portions and from their slopes, the thermal activation energies are calculated. The higher temperature region is called the intrinsic region with activation energies E_1 and the two low temperature regions are known as the extrinsic region with activation energies E_2 and E_3 , respectively.

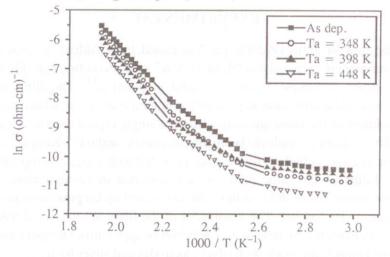


Fig. 2. Plots of $\ln \sigma$ versus 1000/T PbPc thin films annealed in air different temperatures for one hour

Table 1. Variation of activation energy of PbPc thin films coated at different substrate temperatures

Substrate	The state of the state of	Activation Energy (eV)			
Temperature (K)	E_1		E_2		
303	0.77		0.57	0.08	
373	0.74		0.53	0.11	
423	0.70		0.55	0.13	
473	0.67		0.48	_	

Fig. 1. shows the plots of $\ln \sigma$ versus 1000/T for PbPc thin films coated at different substrate temperatures. There are three linear regions except for the film coated at 473 K. This can be due to the absence of a trap level. Table 1 gives the variation of activation energies with substrate temperatures. Most of the organic compounds crystallize via weak van der Walls force and hence, the structure and crystallinity of the grown films can be easily affected by the interaction with the substrate. As the substrate temperature increases, the increase in surface energy causes an increase in grain size and crystallinity resulting in a lowering of activation energy. E_2 and E_3 change in a random manner, since these are due to impurity scattering.

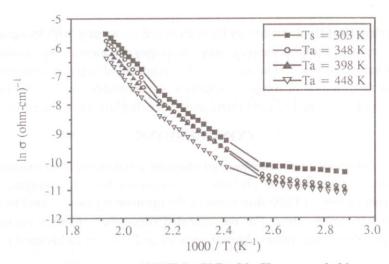


Fig. 3. Plots of ln σ versus 1000/T for PbPc thin films annealed in vacuum at different temperatures for one hour

Table 2. Variation of activation energy of PbPc thin films annealed in air at different temperatures for one hour

Annealing Temperature	Activation Energy (eV)			
(K)	E_1	E ₂	E3	
As deposited	0.77	0.57	0.08	
348	0.79	0.51	0.07	
398	0.82	0.40	0.06	
448	0.86	0.49	0.09	

Figure 2 and 3 give the plots of 1n σ versus 1000/T for the air–annealed and vacuum–annealed samples, respectively. Variations in activation energies with annealing temperature in these cases are collected in Table 2 and 3.

Table 3. Variation of activation energy of PbPc thin films annealed in vacuum at different temperatures for one hour

Annealing Temperature	Activation Energy (eV)			
(K)	E_1	E_2	E ₃	
As deposited	0.77	0.57	0.08	
348	0.81	0.54	0.12	
398	0.85	0.55	0.11	
448	0.87	0.60	0.12	

For these films, the activation energy E_1 is observed to increase with increase in annealing temperature. For most phthalocyanines, oxygen causes an increase in conductivity and a decrease in activation energy 15 . On annealing, the exponential trap distribution is established, confirming that the removal of oxygen impurities is responsible for the modified behaviour. Here again E_2 and E_3 change in a random manner since they are due to impurity scattering.

CONCLUSIONS

Three zone Arrhenius plots are observed showing a transition from extrinsic to intrinsic behaviour. Intrinsic conductivity of phthalocyanines are due to their conjugate structure. The thermal activation energy of PbPc thin films in the intrinsic region is found to decrease with increase in substrate temperature. For the annealed films, the activation energy is found to increase with annealing temperature. Annealing in air and vacuum yields good results.

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